11th ”Trento” Workshop on Advanced Silicon Radiation Detectors

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Book of Abstracts

Contents

Introduction / **182**

3D Sensors for the HL-LHC

Corresponding Author(s): sgrinstein@ifae.es

Planar 1 / **186**

Beam test results of highly irradiated planar and 3D pixel sensors for the Phase II Upgrade of the CMS pixel detector

Corresponding Author(s): daniel.schell@cern.ch

3D / **175**

Beam test results of irradiated 3D pixel sensors for the CMS-TOTEM Precision Proton Spectrometer

Corresponding Author(s): fabio.ravera@cern.ch

Planar 2 / **164**

Characterisation of thin irradiated epitaxial silicon sensors for the CMS phase II pixel upgrade

Corresponding Author(s): matteo.centis.vignali@cern.ch

3D / **188**

Charaterization of 3D module with micro-channel cooling

Corresponding Author(s): cinzia.da.via@cern.ch

HVCMOS 1 / **151**

Charge Collection Properties of depleted Monolithic Active Pixel Sensors

Corresponding Author(s): malte.backhaus@cern.ch

Conference closing / **181**

Close-out

TCAD / **180**

Comprehensive radiation damage test and modelling of p-type silicon detectors for high-luminosity operations

Corresponding Author(s): arianna.morozzi@gmail.com

Technology / **156**

Detector development at the Paul-Scherrer-Institut (PSI)

Corresponding Author(s): dominic.greiffenberg@psi.ch

HVCMOS 1 / **152**

Development of passive pixel sensors using a commercial 150nm CMOS technology on high resistivity silicon

Corresponding Author(s): fabian.huegging@cern.ch, huegging@physik.uni-bonn.de

Introduction / **146**

Electric field, mobility and trapping in Si detectors irradiated with neutrons and protons up to 1e17 n_eq/cm^2

Corresponding Author(s): marko.mikuz@cern.ch

LGAD / **170**

First Inverted Low Gain Avalanche Detector fabrication at IMB-CNM

Corresponding Author(s): mar.carulla@imb-cnm.csic.es

3D / **174**

Initial results from a new generation of 3D Sensors for HL-LHC

Corresponding Author(s): boscardi@fbk.eu, maurizio.boscardin@cern.ch

Planar 3 / **168**

Initial results from the electrical characterisation of planar p-on-n sensors with active/slim-edge for the next generation of FELs

Corresponding Author(s): gianfranco.dallabetta@unitn.it, gian.franco.dalla.betta@cern.ch

HVCMOS 2 / **159**

Investigation on the radiation resistance of HV-CMOS and pin diodes using a Transient Current Technique based on the Two-Photon-Absortion Process

Author(s): Ivan Vila Alvarez[1]

Co-author(s): David Moya Martin [1] ; Francisco Rogelio Palomo Pinto [1] ; Gregor Kramberger [2] ; Javier Gonzalez Sanchez [1] ; Marcos Fernandez Garcia [1] ; Michael Moll [3] ; Richard Jaramillo [4] ; Salvador Hidalgo Villena [5]

[1] *Universidad de Cantabria (ES)*

[2] *Jozef Stefan Institute (SI)*

[3] *CERN*

[4] *IFCA*

[5] *Instituto de Microelectronica de Barcelona (ES)*

Corresponding Author(s): ivan.vila@cern.ch, marcos.fernandez@cern.ch, francisco.rogelio.palomo.pinto@cern.ch, michael.moll@cern.ch, jaramilo@ifca.unican.es, javier.gonzalez.sanchez@cern.ch, gregor.kramberger@ijs.si, hidalgo.salvador@cern.ch, david.moya.martin@cern.ch

Transient Current Techniques (TCT) based on laser-induced photo-currents produced by Single Photon Absorption (SPA) processes have been extensively used during the last two decades as a powerful tool to study many of the properties relevant to operation of semiconductor detectors.

Very recently, an innovative Transient Current Technique was introduced where the free charge carriers are created in a Two-Photon-Absorption (TPA) process induced by a focused femto-second laser pulse with a wavelength of 1300nm. The fact that in a TPA process the absorption of the light depends on the square of the intensity of the light beam used for the current generation allows a localized TPA-induced electron-hole pair creation in a micrometric scale voxel centered on the laser waist. As a consequence, this new technique opens the possibility to carry out a 3D mapping of the sensor's space-charge properties with micrometric resolution.

Due to its intrinsic spatial resolution, the TPA-TCT technique should be a very appropriate choice for the characterization of the alterations of the sensor's active (charge collecting) volume induced by radiation damage and especially for the case of partially depleted sensors as it is the case of the carrier collecting n-well implemented in HV-CMOS sensors.

Planar 3 / **165**

Latest development in HPK/KEK n^+-in-p planar pixel sensors for very high radiation environments

Corresponding Author(s): yoshinobu.unno@kek.jp

LGAD / **169**

Low Gain Avalanche Detectors TCAD Radiation Damage Analysis

Co-author(s): Ivan Vila Alvarez [1] ; Salvador Hidalgo Villena [2]

[1] *Universidad de Cantabria (ES)*

[2] *Instituto de Microelectronica de Barcelona (ES)*

Corresponding Author(s): francisco.rogelio.palomo.pinto@cern.ch, rpalomop@cern.ch, ivan.vila@cern.ch, hidalgo.salvador@cern.ch

Where we present our last results on radiation damage analysis of Low Gain Avalanche Detectors using the Synopsys TCAD suite and different well established radiation damage models. Our main conclusions point to this device could work reasonably well up to ~1e14 n_eq/cm2.

LGAD / **171**

Low Gain Avalanche Diode gallium process flow simulation studies

Corresponding Author(s): evangelos.-.gkougkousis@cern.ch, vagelis.gkougkousis@cern.ch

HVCMOS 1 / **153**

Monolithic CMOS ASIC Developments

Corresponding Author(s): pietroc@slac.stanford.edu

Technology / **155**

New pixel technologies for HL-LHC

Corresponding Author(s): andrea.gaudiello@cern.ch

Planar 3 / **167**

Performance of Edgeless Silicon Pixel Sensors on p-type substrate for the ATLAS High-Luminosity Upgrade

Corresponding Author(s): audrey.ducourthial@cern.ch

Planar 2 / **161**

Pixel Sensor Development for the LHCb VELO Upgrade

Corresponding Author(s): asmund.schiager.folkestad@cern.ch, asmund_sf@hotmail.com

Introduction / **189**

Practical information

Corresponding Author(s): marco.bomben@cern.ch, giovanni.marchiori@cern.ch

Introduction / **144**

Progress in Ultra-Fast Silicon Detectors

Corresponding Author(s): hartmut@scipp.ucsc.edu, hartmut@ucsc.edu

Planar 1 / **147**

Recent results with hybrid pixel assemblies for the CLIC vertex detector

Corresponding Author(s): andreas.nurnberg@cern.ch, andreas.matthias.nurnberg@cern.ch

Planar 2 / **163**

Results on thin n in p Planar Pixels from INFN R&D

Corresponding Author(s): marco.meschini@cern.ch

Technology / **157**

Reverse bias current characterisation of silicon strip sensors and shallow radiation damage generation

Corresponding Author(s): sven.wonsak@cern.ch

HVCMOS 2 / **160**

SPS Test Beam characterisation results with CCPDv4 capacitively coupled to FEI4

Corresponding Author(s): francesco.armando.di.bello@cern.ch

Planar 1 / **148**

Silicon pixel tracking detector with ultra-precise time resolution

Corresponding Author(s): massimiliano.fiorini@cern.ch

3D / **173**

Status of 3D detector activities at CNM

Corresponding Author(s): giulio.pellegrini@cnm.es, giulio.pellegrini@csic.es

LGAD / **172**

Status of LGAD CNM fabrications

Corresponding Author(s): giulio.pellegrini@cnm.es, giulio.pellegrini@csic.es

Planar 3 / **166**

Study of New ADVACAM Active Edge Sensor Technology for ATLAS Upgrade

Corresponding Author(s): tasneem.rashid@cern.ch

TCAD / **177**

TCAD simulations of High-Voltage-CMOS pixel structures for the CLIC vertex detector

Corresponding Author(s): matthew.daniel.buckland@cern.ch

TCAD / **179**

TCAD simulations of LGAD devices using Silvaco software

Corresponding Author(s): marco.bomben@cern.ch

HVCMOS 2 / **158**

TCT measurements of HV-CMOS test structures irradiated with neutrons

Corresponding Author(s): igor.mandic@ijs.si

Planar 1 / **150**

The Belle II SVD Origami Modules

Corresponding Author(s): antonio.paladino@pi.infn.it

Planar 2 / **162**

The Phase 1 upgrade of the CMS pixel detector

Corresponding Author(s): viktor.veszpremi@cern.ch

HVCMOS 1 / **187**

The first reticle size HV-CMOS sensor demonstrator for ATLAS pixel layers

Corresponding Author(s): ivan.peric@kit.edu

Technology / **154**

The impact and persistence of static surface charges on differently passivated silicon strip sensors

Corresponding Author(s): axel.koenig@oeaw.ac.at

Planar 2 / **184**

The upgraded ATLAS Pixel detector and its performance during run-2 in 2015

Corresponding Author(s): didier.ferrere@cern.ch

Introduction / **145**

Tracking in 4 dimensions

Corresponding Author(s): cartiglia@to.infn.it, nicolo.cartiglia@cern.ch

TCAD / **178**

Validation strategy for the simulation of highly irradiated silicon pixel sensors

Corresponding Author(s): joern.schwandt@cern.ch

Introduction / **143**

Welcome

Corresponding Author(s): giovanni.calderini@cern.ch

Planar 1 / **149**

X-rays characterisation of pixelated silicon detectors

Corresponding Author(s): dima.maneuski@glasgow.ac.uk, dzmitry.maneuski@cern.ch